



Docket No. 740756-1974

UNITED STATES PATENT AND TRADEMARK OFFICE

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In re PATENT Application of: )  
Yasuhiko TAKEMURA et al. ) Art Unit 2822  
Application Serial No. 09/321,715 / ) Examiner: M. Wilczewski  
Filed: May 28, 1999 )  
For: SEMICONDUCTOR DEVICE AND PROCESS )  
FOR FABRICATING THE SAME )

AMENDMENT UNDER 37 C.F.R. 1.116

CERTIFICATE OF MAILING

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Commissioner for Patents  
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Sir:

Gwyn J. Cantrell

Responsive to the final Office Action mailed November 27, 2001, the period for  
responding having been extended one (1) month, please amend the above identified application  
as follows.

IN THE CLAIMS:

Please cancel claims 2, 10, 18, 26, 34 and 42.

Please amend the claims as follows.

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1. (Four Times Amended) A method of manufacturing a semiconductor device  
having a plurality of thin film transistors, comprising the steps of:

forming a semiconductor film comprising silicon over a glass substrate;

crystallizing said semiconductor film; and

oxidizing the crystallized semiconductor film to be active layers of said thin film  
transistors in a pressurized atmosphere at a pressure greater than one atmosphere up to 15  
atmospheres and at a temperature lower than a strain point of said glass substrate.